

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET 2SK4196LS — General-Purpose Switching Device **Applications**

Features

- ON-resistance RDS(on)=1.2 Ω (typ.)
- 10V drive

• Input capacitance Ciss=360pF

Specifications

Absolute Maximum Ratings at Ta=25°C

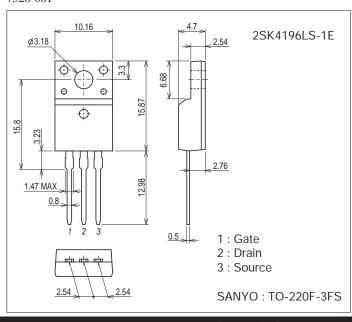
3				
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		500	V
Gate-to-Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	5.5	А
	I _{Dpack*2}	Tc=25°C (SANYO's ideal heat dissipation condition)*3	5.0	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	21	Α
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (SANYO's ideal heat dissipation condition)*3	30	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		83	mJ
Avalanche Current *5	IAV		5.5	Α

Note: *1 Shows chip capability

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Package Dimensions

unit: mm (typ) 7528-001



Product & Package Information

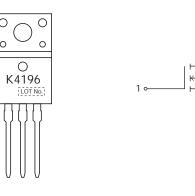
• Package : TO-220F-3FS

• JEITA, JEDEC : SC-67

• Minimum Packing Quantity : 50 pcs./magazine

Marking

Electrical Connection



SANYO Semiconductor Co., Ltd.

http://www.sanyosemi.com/en/network/

^{*2} Package limited

^{*3} SANYO's condition is radiation from backside.

^{*4} VDD=50V, L=5mH, IAV=5.5A (Fig.1)

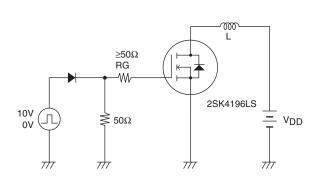
^{*5} L≤5mH, single pulse

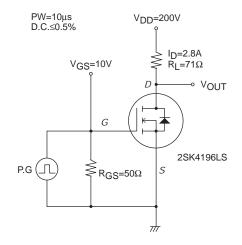
Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Linit	
Parameter	Symbol	Conditions	min	typ	max	Unit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V	
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =400V, V _{GS} =0V			100	μΑ	
Gate-to-Source Leakage Current	IGSS	V _{GS} =±30V, V _{DS} =0V			±100	nA	
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	3		5	V	
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =2.8A	1.3	2.5		S	
Static Drain-to-Source On-State Resistance	R _{DS} (on)	I _D =2.8A, V _G S=10V		1.2	1.56	Ω	
Input Capacitance	Ciss			360		pF	
Output Capacitance	Coss	V _{DS} =30V, f=1MHz		77		pF	
Reverse Transfer Capacitance	Crss			17		pF	
Turn-ON Delay Time	t _d (on)			13		ns	
Rise Time	t _r	San Fig 2		32		ns	
Turn-OFF Delay Time	t _d (off)	See Fig.2		39		ns	
Fall Time	t _f			18		ns	
Total Gate Charge	Qg			14.6		nC	
Gate-to-Source Charge	Qgs	V _{DS} =200V, V _{GS} =10V, I _D =5.5A		3.2		nC	
Gate-to-Drain "Miller" Charge	Qgd			8.8		nC	
Diode Forward Voltage	V _{SD}	I _S =5.5A, V _{GS} =0V		0.9	1.2	V	

Fig.1 Unclamped Inductive Switching Test Circuit

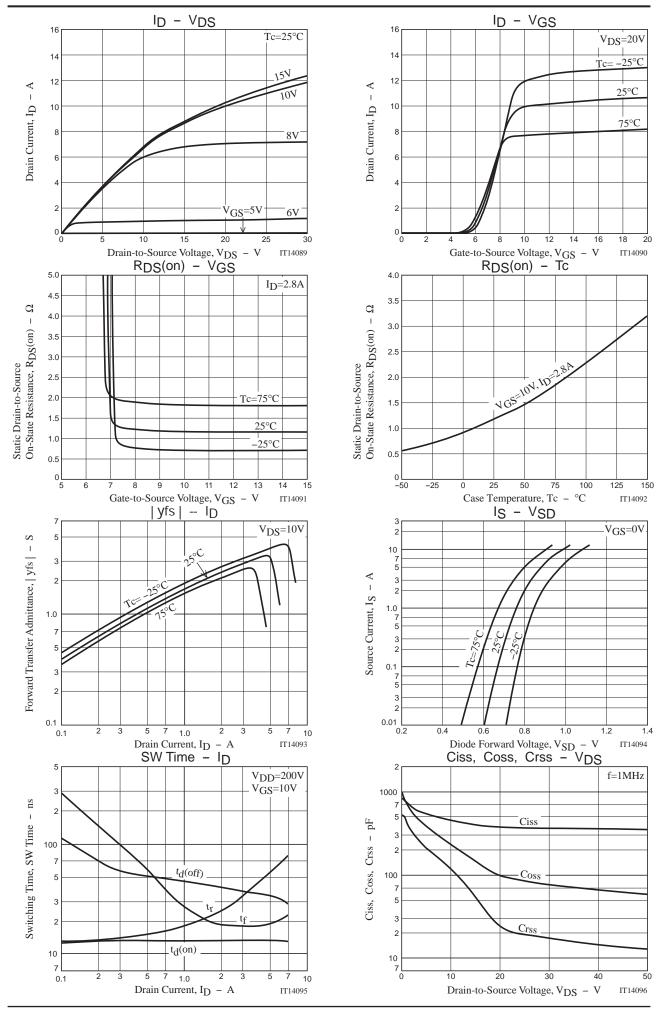
Fig.2 Switching Time Test Circuit

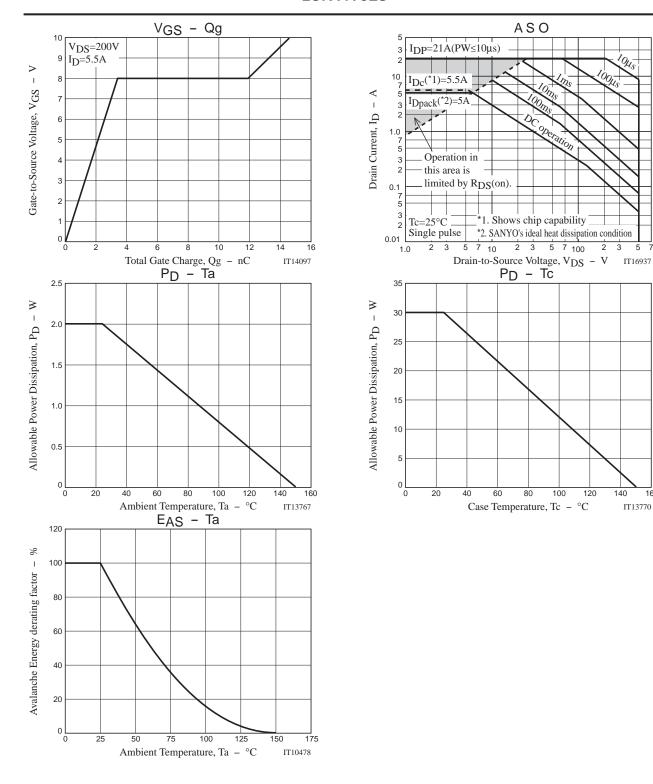




Ordering Information

Device	Package	Shipping	memo
2SK4196LS-1E	TO-220F-3FS	50pcs./magazine	Pb Free





140

160

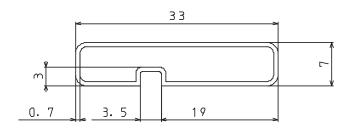
IT13770

Magazine Specification

2SK4196LS-1E

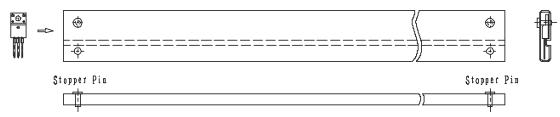
1. Packing Format

Package Name	Magazine Name	I 4.55 to		Maximum Number of devices contained (pcs)			Packing format		
1 4 4 4 4 4 1 4 4 4 4	1020 43 123 14223	l	Inner box	Outer box	Inner BOX	Outer BOX			
TO-220F-3F\$	TO-220F	50	1, 000	4,000	SPD-0V0001 20 magazines contained Dimensions:mm (external) 568×150×55	SPT-081029 4 inner boxes contained Dimensions:mm (external) 590×225×178			



Tolerance=±0, 3mm
Thickness=0, 7±0, 2mm
Length =532, 5±2mm
Material =PVC (Antistatic treatment)

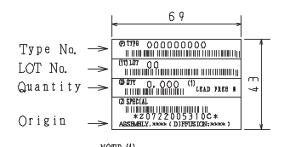
3. Storage method to magazine

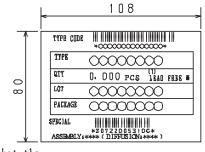


4. Inner box label (unit:mm)



It is a label at the time of factory shigments. The form of a label may change in physical distribution process.



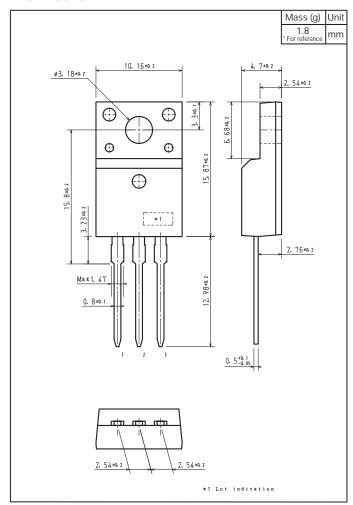


The LEAD FREE * description shows that the surface treatment of the terminal is lead free.

Label		JEITA Phase
LEAD FREE	3	JEITA Phase 3A

Outline Drawing

2SK4196LS-1E



Note on usage: Since the 2SK4196LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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